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Manufacturers of World Class Discrete Semiconductors

CDSH270

SCHOTTKY DIODE

JEDEC DO-35 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR CDSH270 is a Silicon Schottky diode specially designed to replace Germanium diodes manufactured with 1950's technology like the 1N270, 1N277, etc. with 1990's technology. Some advantages of this new technology are lower forward voltage, lower leakage, faster switching speed, and a more robust package.

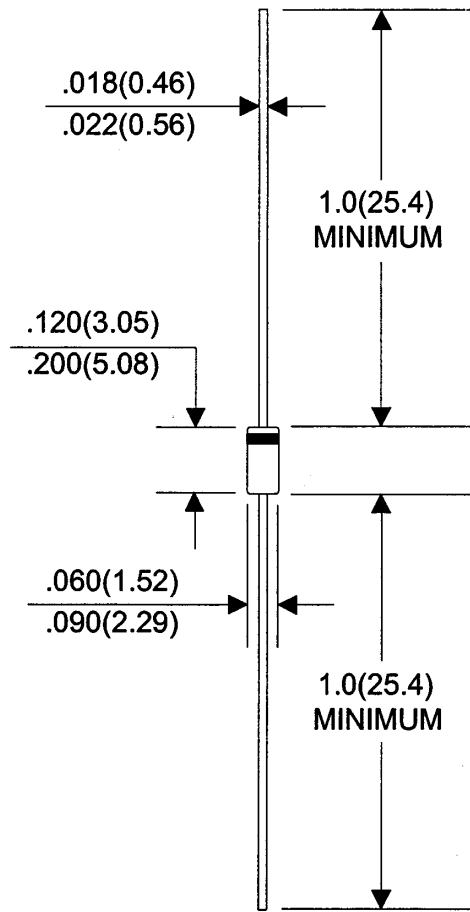
MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

	<u>SYMBOL</u>		<u>UNITS</u>
Peak Repetitive Reverse Voltage	V_{RRM}	100	V
Continuous Forward Current	I_F	100	mA
Peak Forward Current (Repetitive, $t \leq 1\text{s}$, $\delta \leq 0.5\text{s}$)	I_{FRM}	350	mA
Peak Forward Surge Current (Non-Repetitive, $t=10\text{ms}$)	I_{FSM}	750	mA
Power Dissipation	P_D	100	mW
Junction Temperature	T_J	-65 to +125	$^{\circ}\text{C}$
Storage Temperature	T_{stg}	-65 to +150	$^{\circ}\text{C}$
Thermal Resistance	Θ_{JA}	300	$^{\circ}\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

<u>SYMBOL</u>	<u>TEST CONDITIONS</u>	<u>MIN</u>	<u>TYP</u>	<u>MAX</u>	<u>UNITS</u>
I_R	$V_R=50\text{V}$			100	nA
I_R	$V_R=50\text{V}$, $T_A=100^{\circ}\text{C}$			20	μA
V_F	$I_F=1.0\text{mA}$			0.45	V
V_F	$I_F=100\text{mA}$		0.9		V
V_F	$I_F=200\text{mA}$			1.0	V
C_J	$V_R=10\text{V}$, $f=1.0\text{MHz}$		1.2		pF

JEDEC DO-35 CASE - MECHANICAL OUTLINE



All Dimensions in Inches (mm).

This datasheet has been download from:

www.datasheetcatalog.com

Datasheets for electronics components.